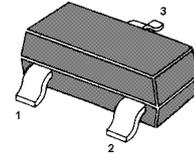
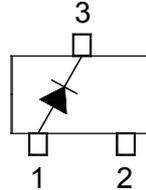


SILICON EPITAXIAL PLANAR DIODE

Band Switching Diode

For VHF band switching applications



Marking Code: **JC**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Power Dissipation	P_D	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Voltage at $I_R = 10\text{ }\mu\text{A}$	V_R	35	-	V
Reverse Current at $V_R = 25\text{ V}$	I_R	-	0.1	μA
Total Capacitance at $V_R = 20\text{ V}$, $f = 1\text{ MHz}$	C_T	-	1	pF
Series Resistance at $I_F = 10\text{ mA}$, $f = 100\text{ MHz}$	r_s	-	0.7	Ω

TYPICAL CHARACTERISTICS

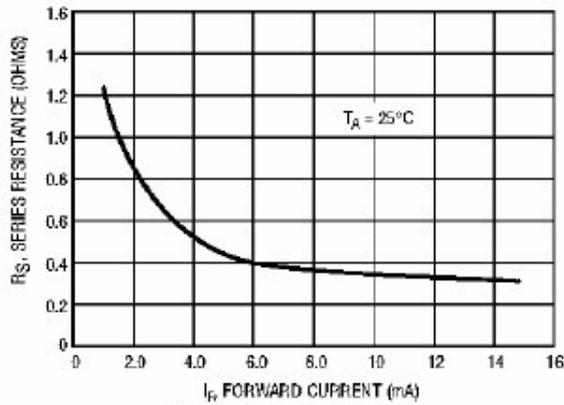


Figure 1. Series Resistance

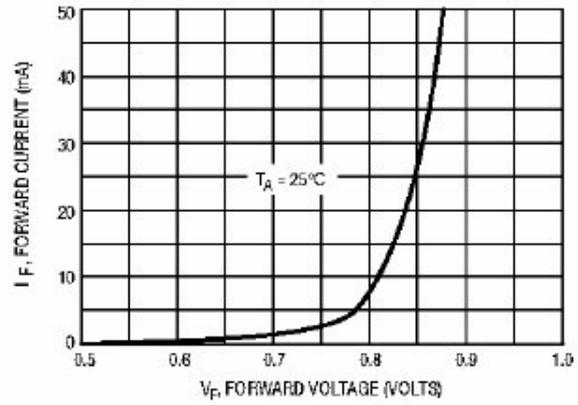


Figure 2. Forward Voltage

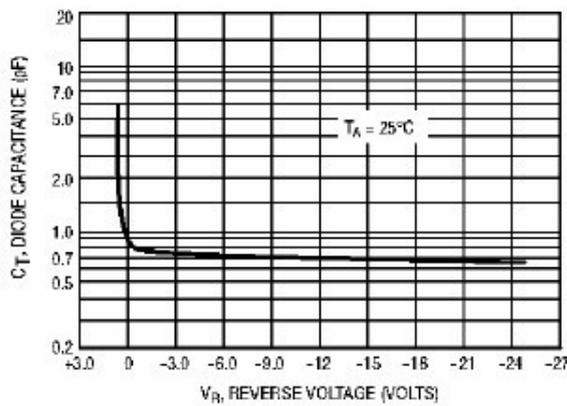


Figure 3. Diode Capacitance

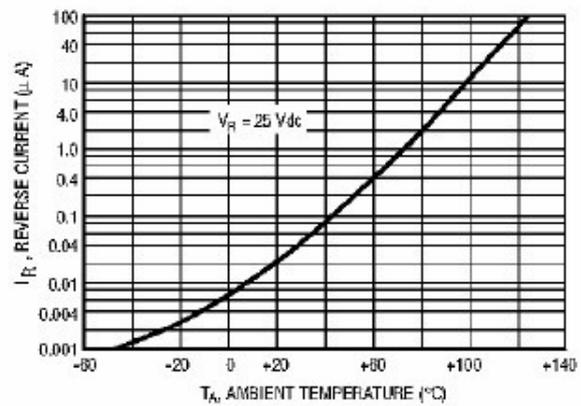


Figure 4. Leakage Current